

SILICON BRIDGE RECTIFIER

REVERSE VOLTAGE : 50 --- 1000 V CURRENT: 0.5 A

Features

- Glass Passivated Die Construction
- High Forward surge capability
- Low Forward Voltage Drop
- High temperature soldering guaranteed: 260°C/10 s
- Lead and body according with RoHS standard

MECHANICAL DATA

- Case styleMBF small outline plastic package
- As Marked on Case
- Epoxy UL: 94V-0
- Mounting Position: Any

MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Single phase,half wave,60 Hz,resistive or inductive load. For capacitive load,derate by 20%.

		Symbols	MB05F	W01F	W02F	W04F	W06F	W08F	W10F	Units
Maximum Recurrent Peak Reverse Voltage		V _{RRM}	50	100	200	400	600	800	1000	Volts
Maximum RMS Voltage		V _{RMS}	35	70	140	280	420	560	700	Volts
Maximum DC Blocking Voltage		V _{DC}	50	100	200	400	600	800	1000	Volts
Maximum Average Forward Rectified Current		I _(O)	0.5 0.8							Amp
Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)		I _{FSM}	30							Amps
Maximum Instantaneous Forward Voltage at 1K5A DC		V _F	1.0							Volts
VR=4.0V, f=1MHz Type junction capacitance		C _j	13							pF
Maximum DC Reverse Current at rated DC blocking voltage	T _A =25 °C	I _R	10							uA
	T _A =125°C		5 500							uA
Operating junction and storage temperature range		T _J T _{STG}	-55 to +150							°C

Note: 1, Mounted on glass epoxy PC board with 1.3mm² solder pad;

2, Mounted on aluminum substrate PC board with 1.3mm² solder pad.

RATINGS AND CHARACTERISTIC CURVES

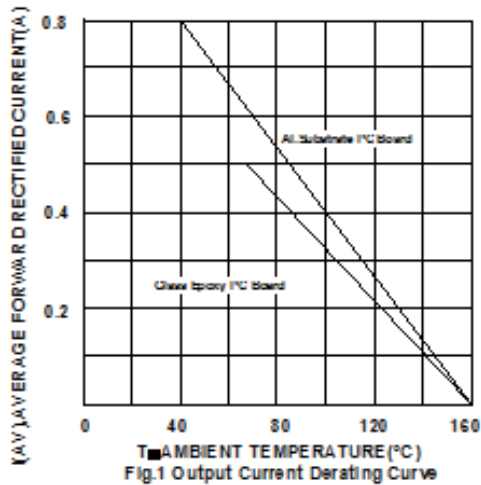


Fig.1 Output Current Derating Curve

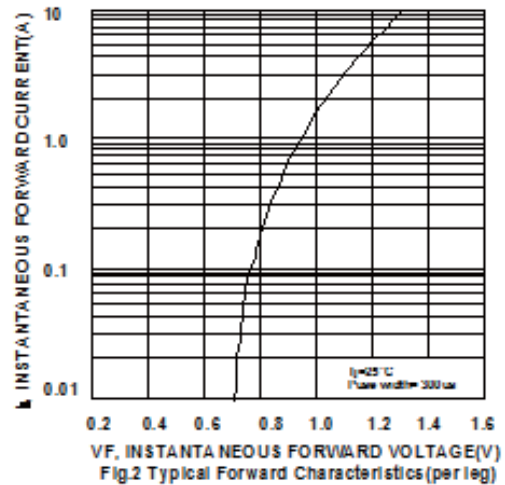


Fig.2 Typical Forward Characteristics (per leg)

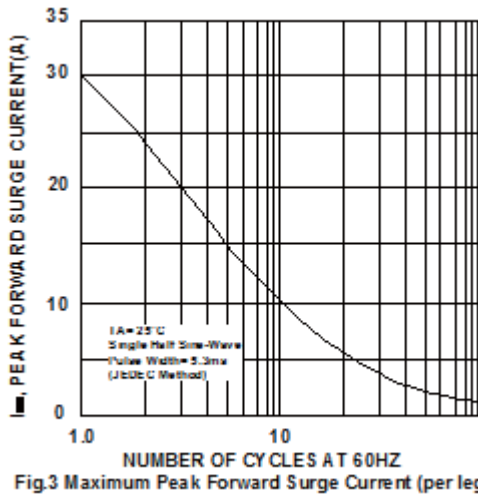


Fig.3 Maximum Peak Forward Surge Current (per leg)

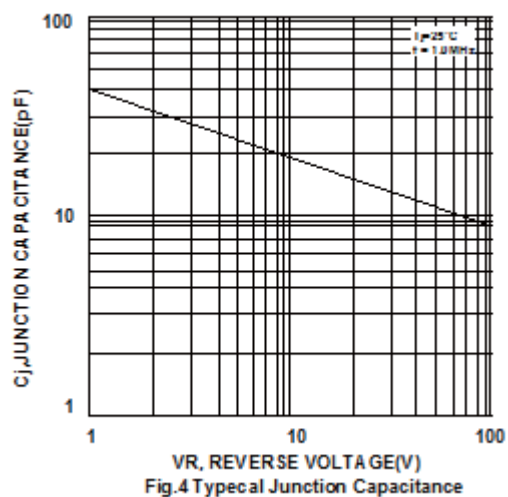


Fig.4 Typical Junction Capacitance

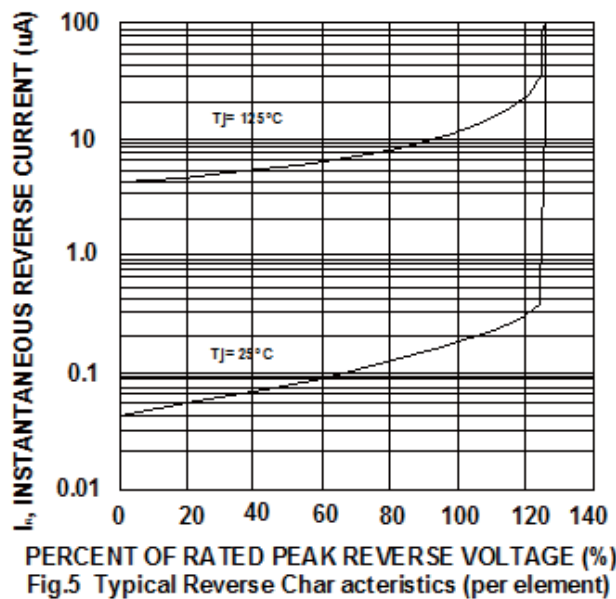
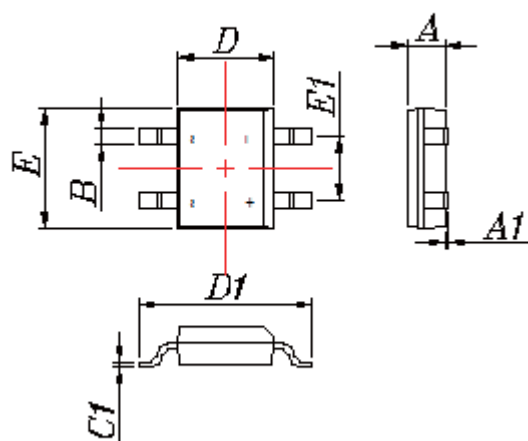


Fig.5 Typical Reverse Characteristics (per element)

MBF



Symbol	Min.	Max.
A	1.30	1.50
A1	--	0.2
B	0.50	0.70
C1	0.15	0.30
D	3.70	3.90
D1	6.70	6.90
E	4.70	4.90
E1	2.45	2.55

单位: *mm*